

ZTX614

NPN Darlington Transistor

- These device is designed for applications requiring extremely high gain at collector currents to 0.5A and high breakdown voltage.
- Sourced from process 06.



Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	120	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	800	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charact	eristics					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{mA}, I_B = 0$	100			V
V _{(BR)CBO}	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	120			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	10			
I _{CBO}	Collector Cutoff Current	$V_{CB} = 60V, I_{E} = 0$			0.1	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 8V, I_{C} = 0$			0.1	μΑ
On Charact	eristics*					
h _{FE}	DC Current Gain	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}$ $I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$	5000 10000			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 800 \text{mA}, I_B = 8 \text{mA}$			1.25	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 800 \text{mA}, V_{BE} = 5 \text{V}$			1.8	V
	e Width ≤ 300μs, Duty Cycle ≤ 1.0%	•	•			1

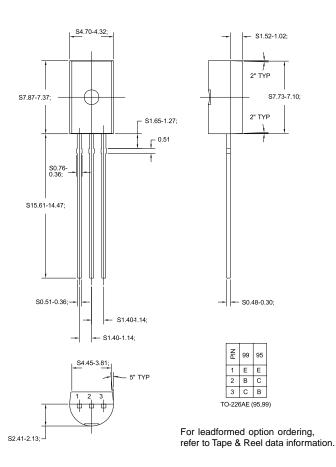
Thermal Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D Total Device Dissipation		1000	mW
_	Derate above 25°C	8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

These ratings are based on a maximum junction temperature of 150°C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Package Dimensions

TO-226



Dimensions in Millimeters

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